

# PNP Transistor Bare Die – TIP117

Rev 1.0 22/08/23

#### Bipolar Darlington Power Transistor in bare die form

Complement to NPN TIP112

#### Features:

- Collector current up to 2A
- Low V<sub>CE</sub>(sat)
- Very high h<sub>FE</sub>
- Solderable back metal
- High Reliability tested grades for Military + Space

### Ordering Information:

The following part suffixes apply:

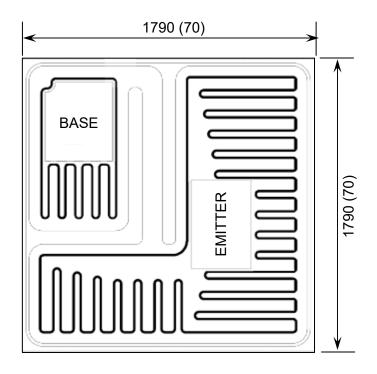
- No suffix Commercial grade die
- "H" Hi-rel grade die + MIL-STD-38534 Class H LAT
- "K" Hi-rel grade die + MIL-STD-38534 Class K LAT.

LAT = Lot acceptance Test.

For information on Hi-Rel LAT flows please see below.

www.siliconsupplies.com\bare-die-lot-qualification

## Die Dimensions in µm (mils)



**DIE BACK = COLLECTOR** 

### **Supply Formats:**

- Default Die in Waffle Pack (100 per tray capacity)
- Sawn Wafer on Tape Specific request
- Unsawn Wafer Specific request
- With additional electrical selection Specific request
- Sawn as pairs or adjacent pair pick Specific request

# **Mechanical Specification**

Die Size (Excluding Saw Street)	1790 x 1790 70.47 x 70.47	μm mils	
Emitter Pad Size	374 x 524 14.72 x 20.63	μm mils	
Base Pad Size	408 x 578 16.06 x 22.76	μm mils	
Die Thickness	260 (±25) 10.2 (±1)	μm mils	
Top Metal Composition	Al		
Back Metal Composition	Ti/Ni/Ag		





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## Absolute Maximum Ratings T<sub>A</sub> = 25°C unless otherwise stated

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V <sub>CBO</sub>	100	V
Collector-Emitter Voltage	V <sub>CEO</sub>	100	V
Emitter-Base Voltage	V <sub>EBO</sub>	5	V
Collector Current - Continuous	Ic	2	A
Collector Current – Peak (t <sub>P</sub> < 5ms)	I <sub>CM</sub>	4	7
Base Current	I <sub>B</sub>	50	mA
Junction Temperature	TJ	150	°C
Storage Temperature	T <sub>stg</sub>	-65 to 150	°C

#### Electrical Characteristics T<sub>A</sub> = 25°C unless otherwise stated

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS							
Collector-Emitter Sustaining Voltage <sup>1</sup>	V <sub>CEO(SUS)</sub>	$I_B = 0, I_C = 30mA$	100	-	-	V	
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>C</sub> = 0	5	-	-	V	
Collector Cut-off Current	I <sub>CEO</sub>	$V_{CE} = 50V, I_{B} = 0$	-	-	2	mA	
Emitter Cut-off Current	I <sub>EBO</sub>	$V_{EB} = 5V, I_{C} = 0$	-	-	2	mA	
Collector Cut-off Current	I <sub>CBO</sub>	V <sub>CB</sub> = 100V, I <sub>E</sub> = 0	-	-	1	mA	
ON CHARACTERISTICS							
Forward-Current Transfer Ratio <sup>1</sup>	h <sub>FE</sub>	I <sub>C</sub> = 1A, V <sub>CE</sub> = 4V	1000	-	-	-	
		$I_C = 2A$ , $V_{CE} = 4V$	500	-	-	-	
Collector-Emitter Saturation Voltage <sup>1</sup>	V <sub>CE(sat)</sub>	$I_{C} = 2A, I_{B} = 8mA$	-	-	2.5	V	
Base-Emitter Saturation Voltage <sup>1</sup>	V <sub>BE(on)</sub>	$I_C = 2A$ , $V_{CE} = 4V$	-	-	2.8	V	
SMALL SIGNAL CHARACTERISTICS <sup>2</sup>							
Small-Signal Current Gain	h <sub>fe</sub>	$V_{CE} = 10V, I_C = 0.75A, f = 1MHz$	25	-	-	-	
Output Capacitance	C <sub>ob</sub>	$V_{CB} = 10V, I_E = 0, f = 0.1MHz$	-	-	150	pF	

<sup>1.</sup> Pulsed duration = 300 µs, duty cycle ≤2.0%

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<sup>2.</sup> Not production testing in die form, characterized by chip design and package verification